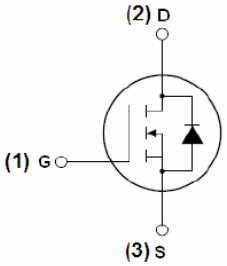
Trench N-Channel PowerMOSFET Wafer Datasheet

FEATURES

- 100V、80A* , N-channel
- $R_{DS(on)}$=8.5mΩ(MAX)
- Ultra low Q_{gd}
- Fast switching

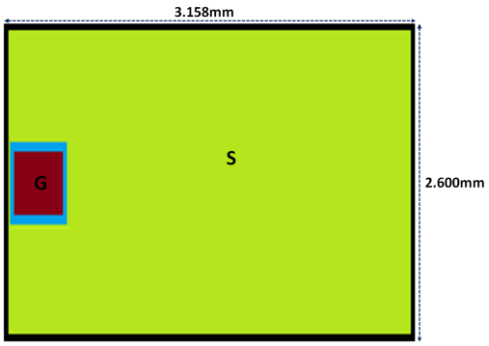


Electrical Characteristics(TJ=25℃)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	100			V	V_{GS}=0V,I_D=250μA
$R_{DS(on)}$	Static Drain-Source On-Resistance		7.2	8.5	mΩ	V_{GS}=10V,I_D=39A
			9.5	12	mΩ	V_{GS}=4.5V,I_D=39A
$V_{GS(th)}$	Gate Threshold Voltage	1.0		2.2	V	V_{DS}=V_{GS},I_D=250μA
I_{DSS}	Drain-to-Source Leakage Current			1	μA	V_{DS}=100V,V_{GS}=0V,T_J=25℃
I_{GSS}	Gate-Body Leakage Current			±100	nA	V_{GS}=±20V
V_{SD}	Body Diode Voltage			1.5	V	V_{GS}=0V,I_{SD}=80A
T_J,T_{stg}	Operating and Storage Temperature Range	-55~+150			℃	

Mechanical Date

Die Size	3158×2600	μm²
Gate Pad Size	254×414	
Source Pad Size	No Passivation	
Scribe Line Size	80	μm
Wafer Diameter	200	mm
Wafer Thickness	200	μm
Passivation Frontside	No Passivation	---
Source Metallization	AlCu , 4.0	μm
Drain Metallization	Ti-Ni-Ag 1K-2K-10K	A
Reject Ink Dot Size	0.51	mm
Recommended Storage Environment	Store in original container, in desiccated nitrogen, with no contamination	



* Electrical characteristics are reported for the reference packaged part (TO-220/263) and cannot be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.